

PROCESS CP310

Small Signal Transistor

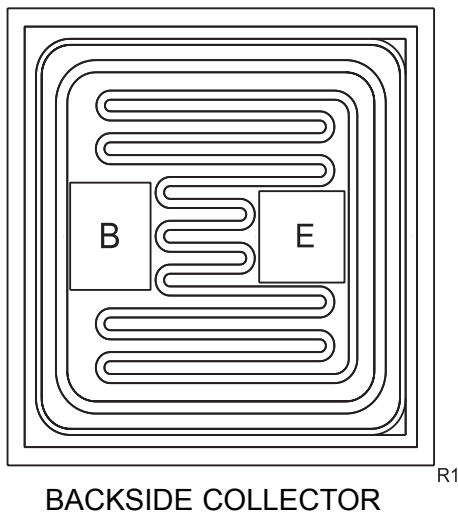
[查询"CP310"供应商](#) NPN High Voltage Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	26 x 26 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	6.1 x 4.9 MILS
Emitter Bonding Pad Area	5.2 x 5.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

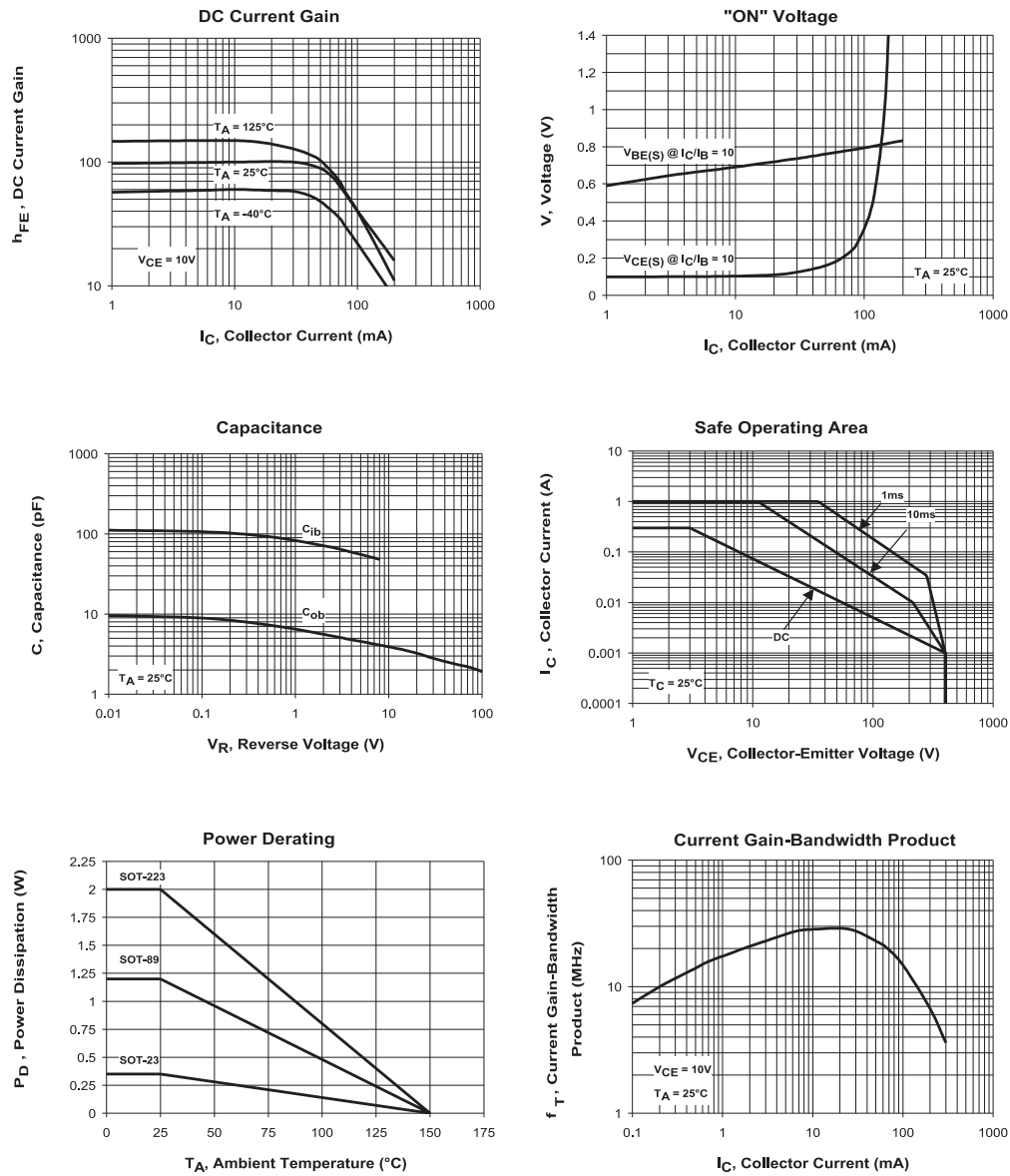
16,880

PRINCIPAL DEVICE TYPES

2N3439
2N3440
CMPTA42
CMPTA44
CMPT6517
CXTA44
CZTA42
CZTA44
MPSA42
MPSA44

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R2 (1-August 2002)



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